

Optocoupler, Phototransistor Output (Dual, Quad Channel), 110 °C Rated

Features

- Operating temperature from - 55 °C to + 110 °C
- Identical Channel to Channel Footprint
- Dual and Quad Packages Feature:
 - Reduced Board Space
 - Lower Pin and Parts Count
 - Better Channel to Channel CTR Match
 - Improved Common Mode Rejection
- Isolation Test Voltage, 5300 V_{RMS}
- Lead-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

Agency Approvals

- UL1577, File No. E52744 System Code H or J, Double Protection
- CSA 93751
- BSI IEC60950 IEC60065
- DIN EN 60747-5-2 (VDE0884)
DIN EN 60747-5-5 pending
Available with Option 1

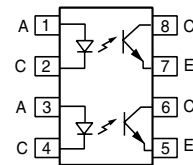
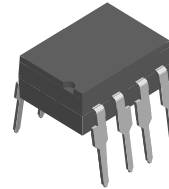
Description

The ILD/Q1615 are multi-channel 110 °C rated phototransistor optocouplers that use GaAs IRLED emitters and high gain NPN phototransistors. These devices are constructed using over/under leadframe optical coupling and double molded insulation technology resulting a withstand test voltage of 7500 VAC-PEAK and a working voltage of 1700 V_{RMS}.

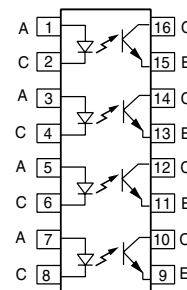
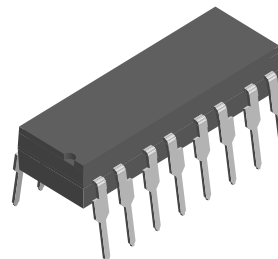
The binned min./max. and linear CTR characteristics make these devices well suited for DC or AC voltage detection. Eliminating the phototransistor base connection provides added electrical noise immunity from the transients found in many industrial control environments.

Because of guaranteed maximum non-saturated and saturated switching characteristics, the ILD/Q1615 can be used in medium speed data I/O and control systems. The binned min./max. CTR specification

Dual Channel



Quad Channel



1179052



allow easy worst case interface calculations for both level detection and switching applications. Interfacing with a CMOS logic is enhanced by the guaranteed CTR at I_F = 1.0 mA.

Order Information

Part	Remarks
ILD1615-1	CTR 40 - 80 %, DIP
ILQ1615-1	CTR 40 - 80 %, DIP
ILD1615-2	CTR 63 - 125 %, DIP
ILQ1615-2	CTR 63 - 125 %, DIP
ILD1615-3	CTR 100 - 200 %, DIP
ILQ1615-3	CTR 100 - 200 %, DIP
ILD1615-4	CTR 160 - 320 %, DIP
ILQ1615-4	CTR 160 - 320 %, DIP

For additional information on the available options refer to Option Information.

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

Input

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	6.0	V
Forward current		I_F	60	mA
Surge current		I_{FSM}	1.5	A
Power dissipation		P_{diss}	100	mW
Derate linearly from 25 °C			1.0	mW/°C

Output

Parameter	Test condition	Symbol	Value	Unit
Collector-emitter breakdown voltage		BV_{CEO}	70	V
Emitter-collector breakdown voltage		BV_{ECO}	7.0	V
Collector current		I_C	50	mA
	$t < 1.0\text{ ms}$	I_C	100	mA
Power dissipation		P_{diss}	150	mW
Derate linearly from 25 °C			1.5	mW/°C

Coupler

Parameter	Test condition	Symbol	Value	Unit
Storage temperature		T_{stg}	- 55 to + 150	°C
Operating temperature		T_{amb}	- 55 to + 110	°C
Soldering temperature	2.0 mm distance from case bottom	T_{sld}	260	°C
Package power dissipation, ILD1615			400	mW
Derate linearly from 25 °C			5.33	mW/°C
Package power dissipation, ILQ1615			500	mW
Derate linearly from 25 °C			6.67	mW/°C
Isolation test voltage	$t = 1.0\text{ sec.}$	V_{ISO}	5300	V_{RMS}
Creepage			≥ 7.0	mm
Clearance			≥ 7.0	mm
Isolation resistance	$V_{IO} = 500\text{ V}, T_{amb} = 25\text{ }^{\circ}\text{C}$	R_{IO}	$\geq 10^{12}$	Ω
	$V_{IO} = 500\text{ V}, T_{amb} = 100\text{ }^{\circ}\text{C}$	R_{IO}	$\geq 10^{11}$	Ω



Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

Input

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	I _F = 10 mA	V _F	1.0	1.15	1.3	V
Breakdown voltage	I _R = 10 μA	V _{BR}	6.0	30		V
Reverse current	V _R = 6.0 V	I _R		0.01	10	μA
Capacitance	V _R = 0 V, f = 1.0 MHz	C _O		25		pF

Output

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector-emitter capacitance	V _{CE} = 5.0 V, f = 1.0 MHz	C _{CE}		6.8		pF
Collector-emitter leakage current, -1, -2	V _{CE} = 10 V	I _{CEO}		2.0	50	nA
Collector-emitter leakage, -3, -4	V _{CE} = 10 V	I _{CEO}		5.0	100	nA
Collector-emitter breakdown voltage	I _{CE} = 0.5 mA	BV _{CEO}	70			V
Emitter-collector breakdown voltage	I _E = 0.1 mA	BV _{ECO}	7.0			V
Package transfer characteristics						
Channel/Channel CTR match	I _F = 10 mA, V _{CE} = 5.0 V	CTR _X / CTR _Y	1 to 1		2 to 1	

Coupler

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Capacitance (input-output)	V _{IO} = 0 V, f = 1.0 MHz	C _{IO}		0.8		pF
Insulation resistance	V _{IO} = 500 V, T _A = 25 °C	R _S	10 ¹²	10 ¹⁴		Ω
Channel to channel isolation			500			VAC

Current Transfer Ratio

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Current Transfer Ratio (collector-emitter saturated)	I _F = 10 mA, V _{CE} = 0.4 V	ILD1615-1 ILQ1615-1	CTR _{CEsat}		25		%
		ILD1615-2 ILQ1615-2	CTR _{CEsat}		40		%
		ILD1615-3 ILQ1615-3	CTR _{CEsat}		60		%
		ILD1615-4 ILQ1615-4	CTR _{CEsat}		100		%

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Current Transfer Ratio (collector-emitter)	$I_F = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	ILD1615-1 ILQ1615-1	CTR_{CE}	40	60	80	%
	$I_F = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	ILD1615-1 ILQ1615-1	CTR_{CE}	13	30		%
	$I_F = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	ILD1615-2 ILQ1615-2	CTR_{CE}	63	80	125	%
	$I_F = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	ILD1615-2 ILQ1615-2	CTR_{CE}	22	45		%
	$I_F = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	ILD1615-3 ILQ1615-3	CTR_{CE}	100	150	200	%
	$I_F = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	ILD1615-3 ILQ1615-3	CTR_{CE}	34	70		%
	$I_F = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	ILD1615-4 ILQ1615-4	CTR_{CE}	160	200	320	%
	$I_F = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	ILD1615-4 ILQ1615-4	CTR_{CE}	56	90		%

Switching Characteristics

Non-saturated

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Turn-on time	$I_F = 10 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 75 \Omega,$ 50 % of V_{PP}	t_{on}		3.0		μs
Rise time	$I_F = 10 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 75 \Omega,$ 50 % of V_{PP}	t_r		2.0		μs
Turn-off time	$I_F = 10 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 75 \Omega,$ 50 % of V_{PP}	t_{off}		2.3		μs
Fall time	$I_F = 10 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 75 \Omega,$ 50 % of V_{PP}	t_f		2.0		μs
Propagation H-L	$I_F = 10 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 75 \Omega,$ 50 % of V_{PP}	t_{PHL}		1.1		μs
Propagation L-H	$I_F = 10 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 75 \Omega,$ 50 % of V_{PP}	t_{PLH}		2.5		μs

Saturated

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Turn-on time	$I_F = 20 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 1.0 \text{ k}\Omega,$ $V_{HT} = 1.5 \text{ V}$	ILD1615-1 ILQ1615-1	t_{on}		3.0		μs
	$I_F = 10 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 1.0 \text{ k}\Omega,$ $V_{HT} = 1.5 \text{ V}$	ILD1615-2 ILQ1615-2	t_{on}		4.3		μs
		ILD1615-3 ILQ1615-3	t_{on}		4.3		μs
	$I_F = 5.0 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 1.0 \text{ k}\Omega,$ $V_{HT} = 1.5 \text{ V}$	ILD1615-4 ILQ1615-4	t_{on}		6.0		μs
Rise time	$I_F = 20 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 1.0 \text{ k}\Omega,$ $V_{HT} = 1.5 \text{ V}$	ILD1615-1 ILQ1615-1	t_r		2.0		μs
	$I_F = 10 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 1.0 \text{ k}\Omega,$ $V_{HT} = 1.5 \text{ V}$	ILD1615-2 ILQ1615-2	t_r		2.8		μs
		ILD1615-3 ILQ1615-3	t_r		2.8		μs
	$I_F = 5.0 \text{ mA}, V_{CC} = 5.0 \text{ V}, R_L = 1.0 \text{ k}\Omega,$ $V_{HT} = 1.5 \text{ V}$	ILD1615-4 ILQ1615-4	t_r		4.6		μs



Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Turn-off time	$I_F = 20 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$, $V_{HT} = 1.5 \text{ V}$	ILD1615-1 ILQ1615-1	t_{off}		18		μs
	$I_F = 10 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$, $V_{HT} = 1.5 \text{ V}$	ILD1615-2 ILQ1615-2	t_{off}		25		μs
		ILD1615-3 ILQ1615-3	t_{off}		25		μs
	$I_F = 5.0 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$, $V_{HT} = 1.5 \text{ V}$	ILD1615-4 ILQ1615-4	t_{off}		25		μs
Fall time	$I_F = 20 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$, $V_{HT} = 1.5 \text{ V}$	ILD1615-1 ILQ1615-1	t_f		11		μs
	$I_F = 10 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$, $V_{HT} = 1.5 \text{ V}$	ILD1615-2 ILQ1615-2	t_f		14		μs
		ILD1615-3 ILQ1615-3	t_f		14		μs
	$I_F = 5.0 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$, $V_{HT} = 1.5 \text{ V}$	ILD1615-4 ILQ1615-4	t_f		15		μs
Propagation H-L	$I_F = 5.0 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$, $V_{HT} = 1.5 \text{ V}$	ILD1615-1 ILQ1615-1	t_{PHL}		1.6		μs
		ILD1615-2 ILQ1615-2	t_{PHL}		2.6		μs
		ILD1615-3 ILQ1615-3	t_{PHL}		2.6		μs
		ILD1615-4 ILQ1615-4	t_{PHL}		5.4		μs
Propagation L-H	$I_F = 5.0 \text{ mA}$, $V_{CC} = 5.0 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$, $V_{HT} = 1.5 \text{ V}$	ILD1615-1 ILQ1615-1	t_{PLH}		8.6		μs
		ILD1615-2 ILQ1615-2	t_{PLH}		7.2		μs
		ILD1615-3 ILQ1615-3	t_{PLH}		7.2		μs
		ILD1615-4 ILQ1615-4	t_{PLH}		7.4		μs

Common Mode Transient Immunity

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Common mode rejection output high	$V_{CM} = 50 \text{ V}_{P-P}$, $R_L = 1.0 \text{ k}\Omega$, $I_F = 0 \text{ mA}$	CM_H		5000		$\text{V}/\mu\text{s}$
Common mode rejection output low	$V_{CM} = 50 \text{ V}_{P-P}$, $R_L = 1.0 \text{ k}\Omega$, $I_F = 10 \text{ mA}$	CM_L		5000		$\text{V}/\mu\text{s}$
Common mode coupling capacitance		C_{CM}		0.01		pF

Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

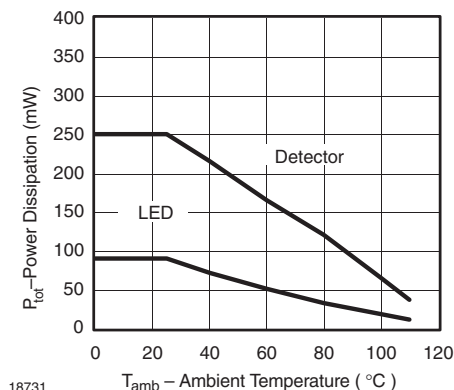


Figure 1. Permissible Power Dissipation vs. Temperature Non-Saturation Operation

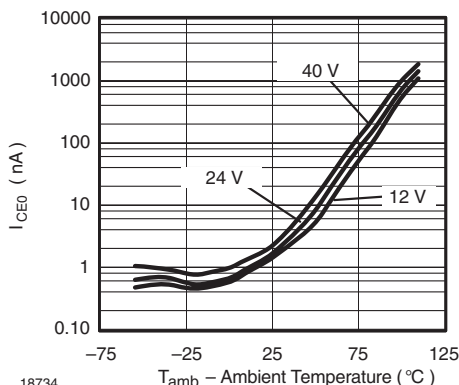


Figure 4. Collector to Emitter Dark Current vs. Ambient Temperature

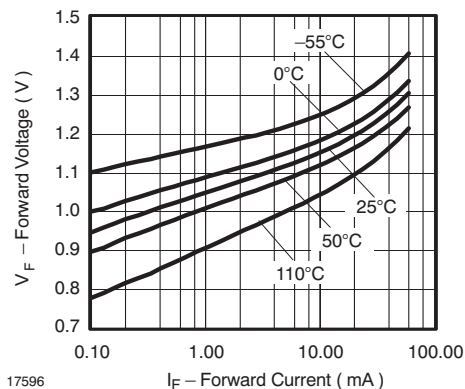


Figure 2. Forward Voltage vs. Forward Current

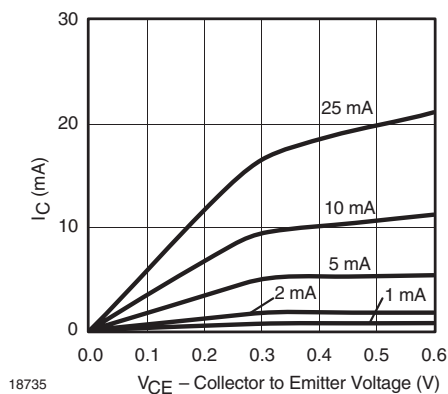


Figure 5. Normalized Current vs. Collector Emitter Saturation Voltage

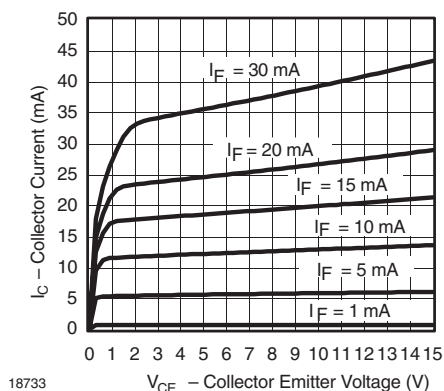


Figure 3. Collector Current vs. Collector Emitter Voltage

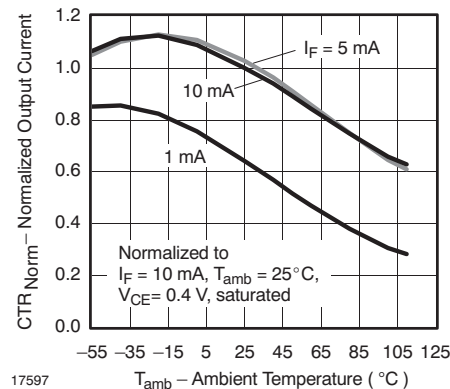


Figure 6. Normalized Current Transfer Ratio vs. Ambient Temperature

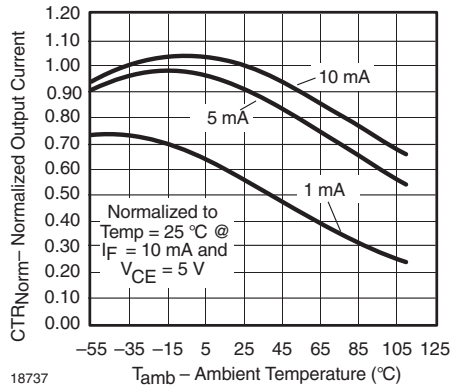


Figure 7. Normalized CTR vs. Temperature

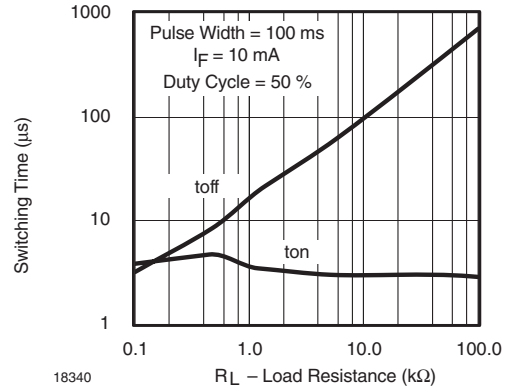


Figure 10. Forward Resistance vs. Forward Current

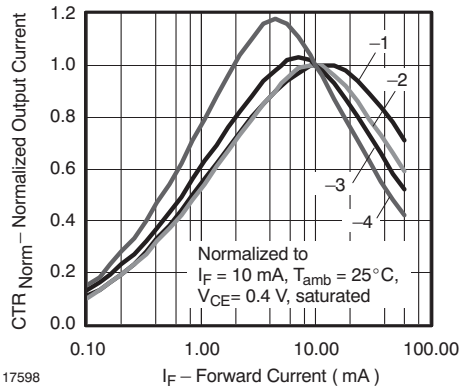


Figure 8. Normalized CTR vs. Forward Current

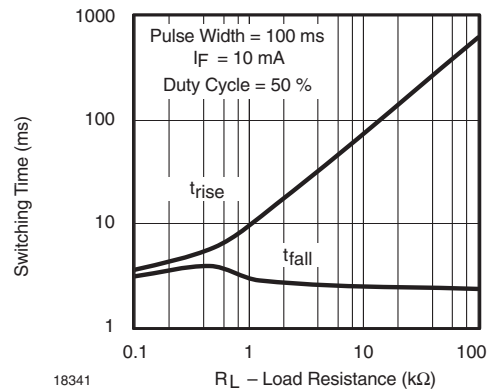


Figure 11. Forward Resistance vs. Forward Current

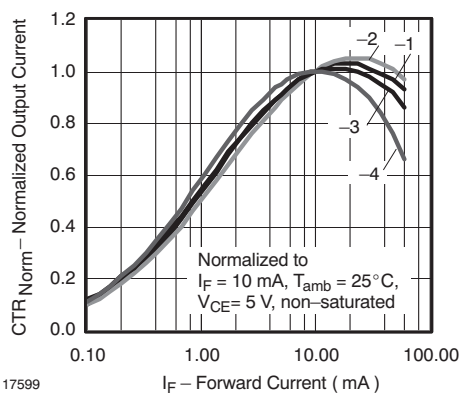


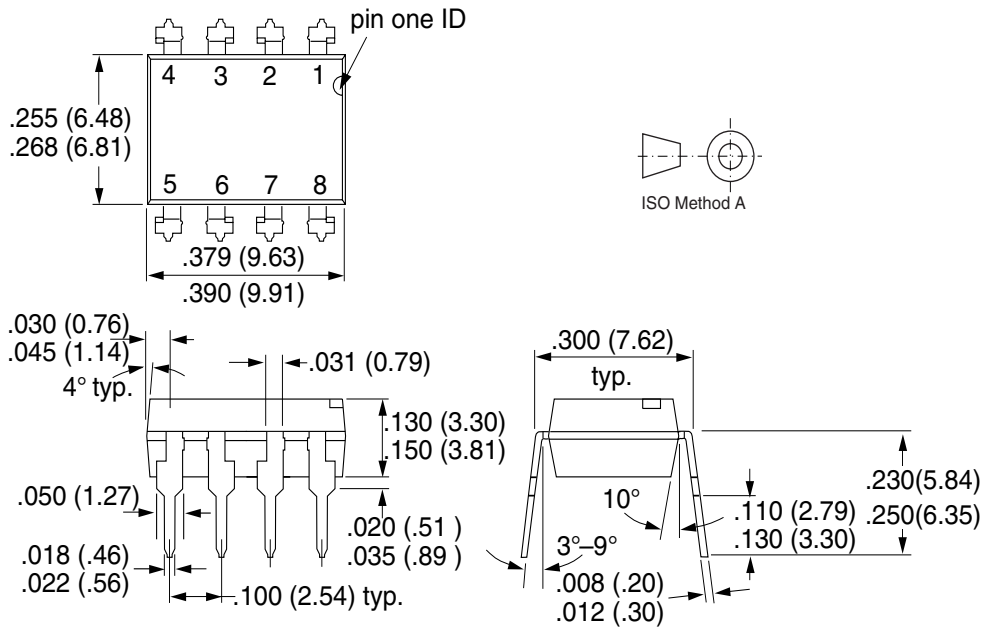
Figure 9. Normalized CTR vs. Forward Current

ILD1615/ ILQ1615

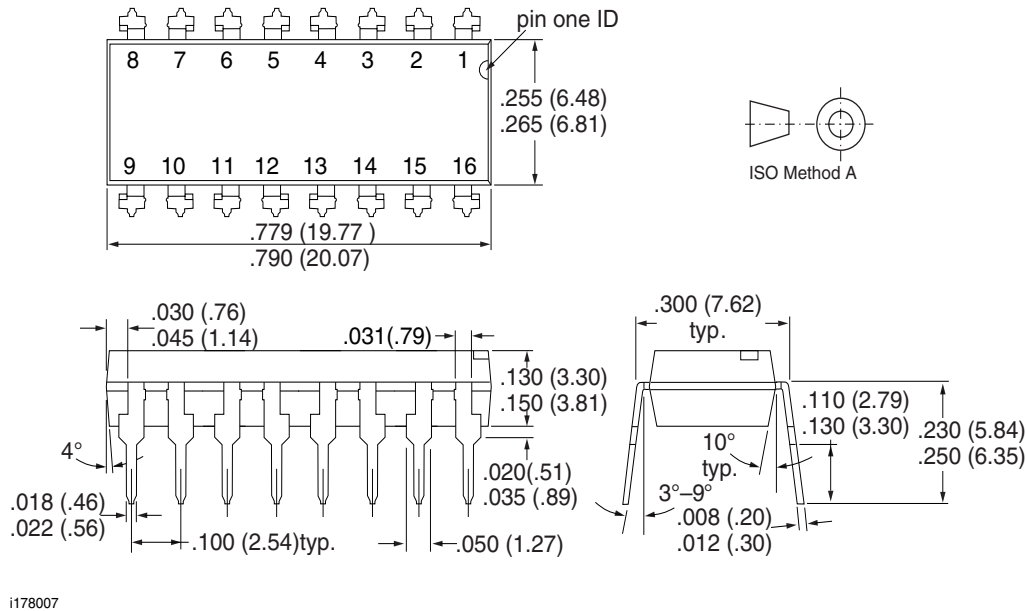


Vishay Semiconductors

Package Dimensions in Inches (mm)



Package Dimensions in Inches (mm)





Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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